

4/19/2011

PRODUCT RELIABILITY REPORT FOR

71M6545

Maxim Integrated Products

4401 South Beltwood Parkway Dallas, TX 75244-3292

Prepared by:

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Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Maxim products:

71M6545

In addition, Maxim's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp($(Ea/k)^*(1/Tu - 1/Ts)$) = tu/ts AfT = Acceleration factor due to Temperature tu = Time at use temperature (e.g. 55°C) ts = Time at stress temperature (e.g. 125°C) k = Boltzmann's Constant (8.617 x 10-5 eV/°K) Tu = Temperature at Use (°K) Ts = Temperature at Stress (°K) Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B*(Vs - Vu)) AfV = Acceleration factor due to Voltage Vs = Stress Voltage (e.g. 7.0 volts) Vu = Maximum Operating Voltage (e.g. 5.5 volts) B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts * AfV * AfT * N * 2) X = Chi-Sq statistical upper limit N = Life test sample size Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE:	MTTF (YRS):	26556	FITS:	4.3			
	DEVICE HOURS:	213155768	FAILS:	0			
Only data from Operating Life or similar stresses are used for this calculation.							
The parameters used to calculate this failure rate are as follows:							
Cf: 60% Ea:	0.7 B: 0	Tu: 2	25 °C	Vu: 3.3 Volts			
The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. Bold Product Number denotes specific product data.							

Device Information	on:								
Process:		TSMC 0.25um, Mixed signal, Embedded flash, General Purpose, Double poly Quad metal, 2.5V/3.3V						uble	
Passivation: Die Size: Number of Trans Interconnect: Gate Oxide Thic		SiO/SiN = 125 x 152 1199824 Aluminum	= 1000nm/70)0nm					
ESD HBM									
DESCRIPTION	DATE	CODE/PRODUCT	r/LOT	CONDITION	REA	DPOIN	QTY	FAILS	FA#
ESD SENSITIVITY	1042	71M6543	QB112428AE	JESD22-A114 HBM 1000 VOLTS	1	PUL'S	5	0	
ESD SENSITIVITY	1042	71M6543	QB112428AE	JESD22-A114 HBM 1500 VOLTS	1	PUL'S	5	0	
ESD SENSITIVITY	1042	71M6543	QB112428AE	JESD22-A114 HBM 2000 VOLTS	1	PUL'S	5	0	
ESD SENSITIVITY	1042	71M6543	QB112428AE	JESD22-A114 HBM 3000 VOLTS	1	PUL'S	5	0	
ESD SENSITIVITY	1042	71M6543	QB112428AE	JESD22-A114 HBM 4000 VOLTS	1	PUL'S	5	0	
					Tota	l:		0	
LATCH-UP									
DESCRIPTION	DATE	CODE/PRODUCT	ſ/LOT	CONDITION	REA	DPOIN	QTY	FAILS	FA#
LATCH-UP I	1042	71M6543	QB112428AE	E JESD78A, I-TEST 25C 100mA			6	0	
LATCH-UP I	1042	71M6543	QB112428AE	E JESD78A, I-TEST 25C 250mA			6	0	
LATCH-UP V	1042	71M6543	QB112428AE	JESD78A, V-SUPPLY TEST 25C			6	0	
					Tota	l:		0	

OPERATING LIFE						
DESCRIPTION	DATE CODE/PRODUC	T/LOT COM	NDITION	READPOIN	QTY FAILS	FA#
HIGH TEMP OP LIFE	0222 78M6613	26728 1250	C, 3.6 VOLTS	1000 HRS	76 0	
HIGH TEMP OP LIFE	1026 71M6103	26803 1250	C, 3.3 VOLTS	500 HRS	200 0	
HIGH TEMP OP LIFE	1042 71M6543	QB112428AE 1250	C, 3.3 VOLTS	500 HRS	100 0	
				Total:	0	
FAILURE RATE:	MTTF (YRS	S): 26556	FITS:	4.3		
	DEVICE HOUR	S: 213155768	FAILS:	0		